

# FDFC3N108

## N-Channel 1.8V Specified PowerTrench<sup>®</sup> MOSFET with Schottky Diode

### General Description

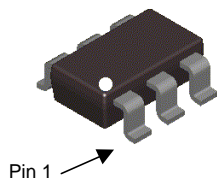
This N-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It is combined with a low forward drop Schottky that is isolated from the MOSFET, providing a compact power solution for battery power management and DC/DC converter applications.

### Applications

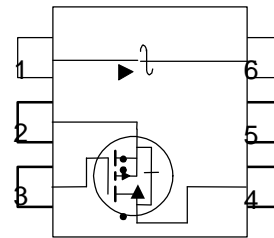
- Battery management/Charger Application
- DC/DC Conversion

### Features

- 3 A, 20 V  $R_{DS(ON)} = 70 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$   
 $R_{DS(ON)} = 95 \text{ m}\Omega @ V_{GS} = 2.5 \text{ V}$
- Low gate charge
- High performance trench technology for extremely low  $R_{DS(ON)}$



SuperSOT™-6



### MOSFET Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage	20	V	
V <sub>GSS</sub>	Gate-Source Voltage	±12	V	
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	3	A	
	– Pulsed	12		
P <sub>D</sub>	Maximum Power Dissipation (Note 1a)	0.96	W	
		(Note 1b)		0.90
		(Note 1c)		0.70
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	–55 to +150	°C	

### Schottky Diode Maximum Ratings

V <sub>RRM</sub>	Repetitive Peak reverse voltage	20	V
I <sub>O</sub>	Average Forward Current	2.0	A

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	60	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.108	FDFC3N108	7"	8mm	3000 units

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

#### Off Characteristics

$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		12		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate–Body Leakage	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

#### On Characteristics

(Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.5	0.9	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 4.5\text{ V}, I_D = 3\text{ A}$ $V_{GS} = 2.5\text{ V}, I_D = 2.5\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 3\text{ A}, T_J = 125^\circ\text{C}$		56 73 78	70 95 106	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	12			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 3\text{ A}$		10		S

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		355		pF
$C_{oss}$	Output Capacitance			85		pF
$C_{rss}$	Reverse Transfer Capacitance			45		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		2.0		$\Omega$

#### Switching Characteristics

(Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A}, V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		6	12	ns
$t_r$	Turn–On Rise Time			7	14	ns
$t_{d(off)}$	Turn–Off Delay Time			20	36	ns
$t_f$	Turn–Off Fall Time			1	2	ns
$Q_g$	Total Gate Charge	$V_{DS} = 10\text{ V}, I_D = 3\text{ A}, V_{GS} = 4.5\text{ V}$		3.5	4.9	nC
$Q_{gs}$	Gate–Source Charge			0.7		nC
$Q_{gd}$	Gate–Drain Charge			1.0		nC

#### Drain–Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain–Source Diode Forward Current				0.8	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.8\text{ A}$ (Note 2)			1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 3\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$		12		nS
$Q_{rr}$	Diode Reverse Recovery Charge			3		nC

#### Schottky Diode Characteristic

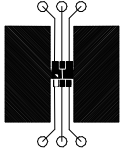
$I_R$	Reverse Leakage	$V_R = 20\text{ V}$	$T_J = 25^\circ\text{C}$			250	$\mu\text{A}$
			$T_J = 100^\circ\text{C}$			10	mA
$V_F$	Forward Voltage	$I_F = 1\text{ A}$			363	425	mV
					449	550	

## Electrical Characteristics

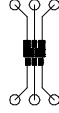
$T_A = 25^\circ\text{C}$  unless otherwise noted

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



- a)  $130^\circ\text{C/W}$  when mounted on a  $0.125\text{ in}^2$  pad of 2 oz. copper.



- b)  $140^\circ\text{C/W}$  when mounted on a  $.004\text{ in}^2$  pad of 2 oz copper



- c)  $180^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty Cycle  $< 2.0\%$

Typical Characteristics

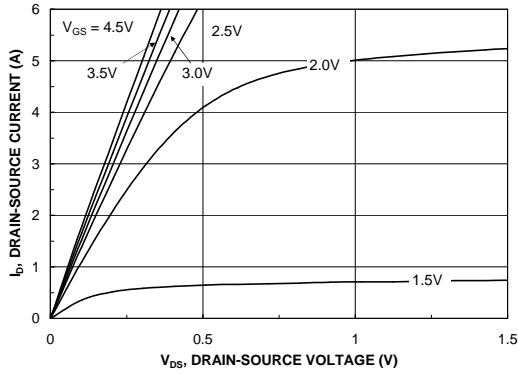


Figure 1. On-Region Characteristics.

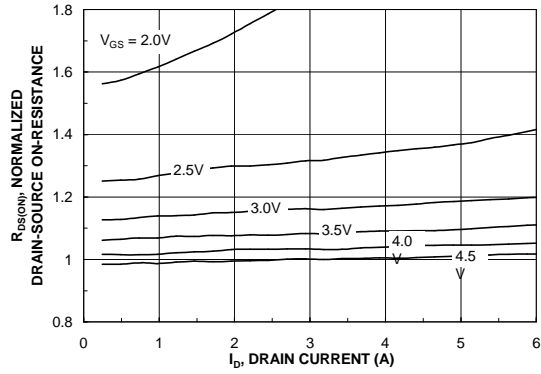


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

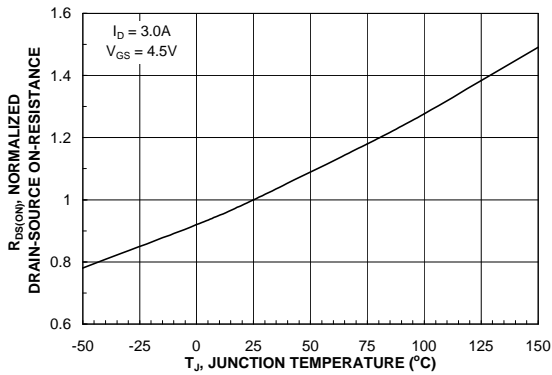


Figure 3. On-Resistance Variation with Temperature.

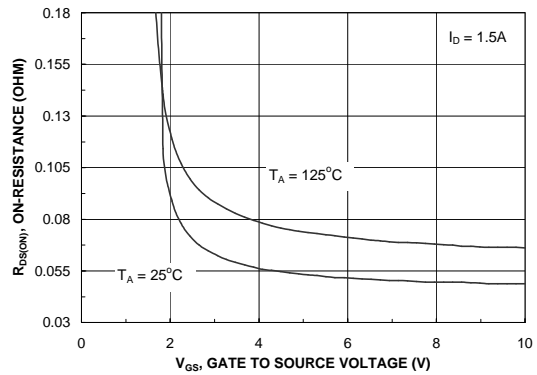


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

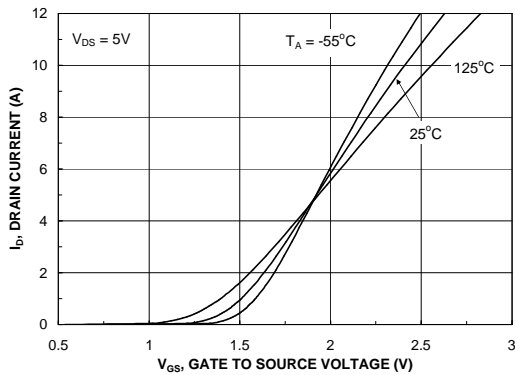


Figure 5. Transfer Characteristics.

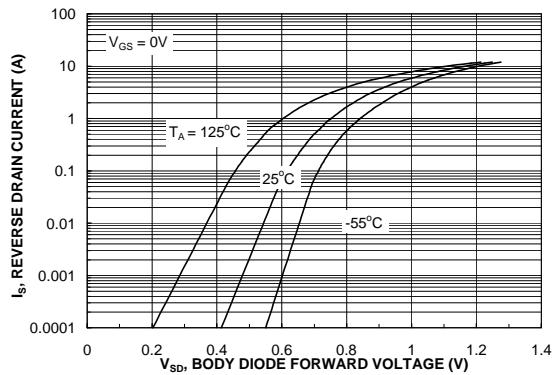


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

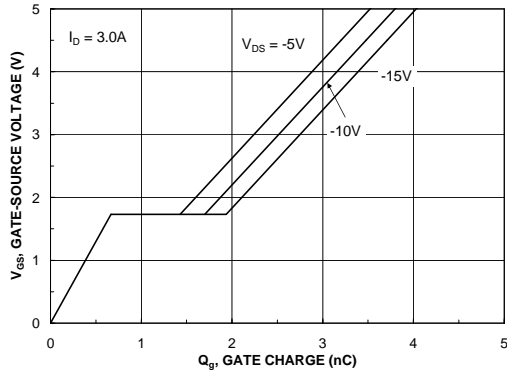


Figure 7. Gate Charge Characteristics.

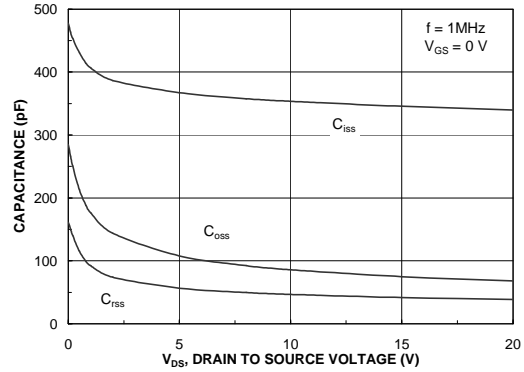


Figure 8. Capacitance Characteristics.

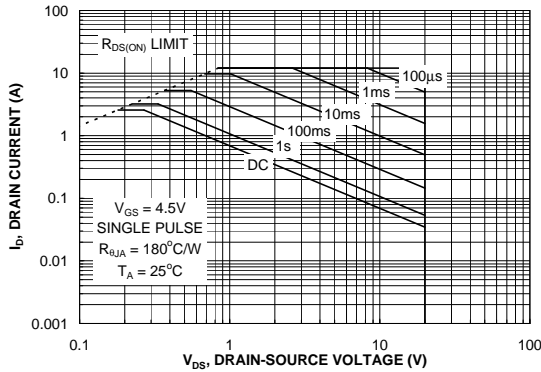


Figure 9. Schottky Diode Forward Voltage.

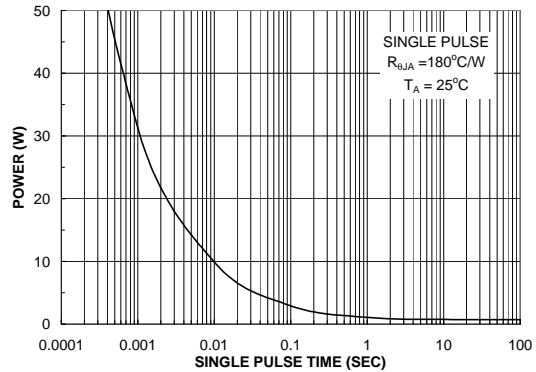


Figure 10. Schottky Diode Reverse Current.

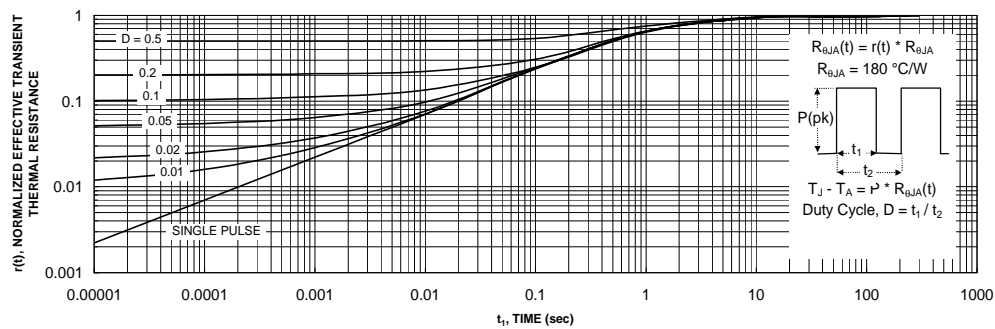


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b  
 Transient thermal response will change depending on the circuit board design.

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	IntelliMAX™	POP™	SPM™
ActiveArray™	FASTR™	ISOPLANAR™	Power247™	Stealth™
Bottomless™	FPST™	LittleFET™	PowerEdge™	SuperFET™
CoolFET™	FRFET™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CROSSVOLT™	GlobalOptoisolator™	MicroFET™	PowerTrench®	SuperSOT™-6
DOMET™	GTO™	MicroPak™	QFET®	SuperSOT™-8
EcoSPARK™	HiSeC™	MICROWIRE™	QS™	SyncFET™
E <sup>2</sup> CMOS™	ꝑC™	MSX™	QT Optoelectronics™	TinyLogic®
EnSigna™	i-Lo™	MSXPro™	Quiet Series™	TINYOPTO™
FACT™	ImpliedDisconnect™	OCX™	RapidConfigure™	TruTranslation™
FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
Across the board. Around the world.™		OPTOLOGIC®	µSerDes™	UltraFET®
The Power Franchise®		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
Programmable Active Droop™		PACMAN™	SMART START™	VCX™

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.